TAIWAN SEMICONDUCTOR

RoHS COMPLIANCE

TSM1N60S

600V N-Channel Power MOSFET

TO-92

Pin Definition:
1. Gate
2. Drain
3. Source

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$(Ω)	I_D (A)
600	11 @ V_{GS} =10V	0.3

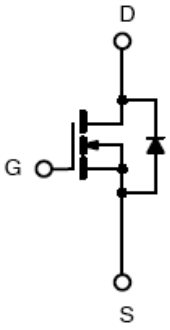
General Description

The TSM1N60S is used an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain- to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

Features

- Robust high voltage termination
- Avalanche energy specified
- Diode is characterized for use in bridge circuits
- Source to Drain diode recovery time comparable to a discrete fast recovery diode.
- I_{DSS} and $V_{DS(on)}$ specified at elevated temperature

Block Diagram



N-Channel MOSFET

Ordering Information

Part No.	Package	Packing
TSM1N60SCT B0	TO-92	1Kpcs / Bulk
TSM1N60SCT A3	TO-92	2Kpcs / Ammo

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current	I_D	0.3	A
Pulsed Drain Current	I_{DM}	1.2	A
Continuous Source Current (Diode Conduction)[a,b]	I_S	1	A
Single Pulse Drain to Source Avalanche Energy (V_{DD} = 100V, V_{GS}=10V, I_{AS}=2A, L=10mH, R_G=25Ω)	EAS	50	mJ
Maximum Power Dissipation @Ta = 25°C	P_D	3	W
Operating Junction Temperature	T_J	+150	°C
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

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Thermal Performance

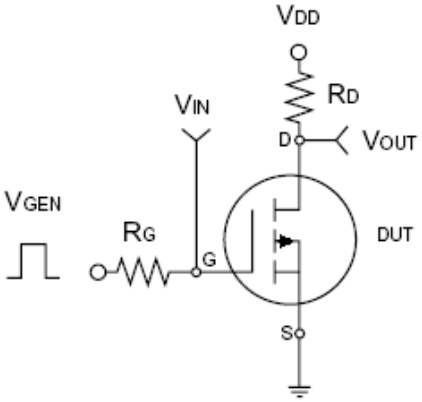
Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	T_L	10	S
Thermal Resistance - Junction to Ambient	$R\Theta_{JA}$	50	°C/W

Notes: Surface mounted on FR4 board t ≤ 10sec

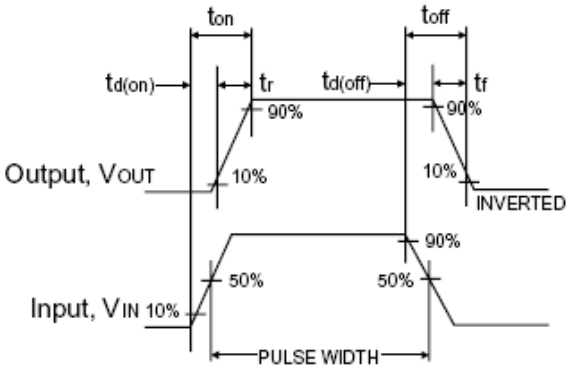
Electrical Specifications (Ta=25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250uA	BV_{DSS}	600	--	--	V
Drain-Source On-State Resistance	V_{GS} = 10V, I_D = 0.3A	$R_{DS(ON)}$	--	11	13	Ω
Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250uA	$V_{GS(TH)}$	2.0	--	4.0	V
Zero Gate Voltage Drain Current	V_{DS} = 600V, V_{GS} = 0V	I_{DSS}	--	--	10	uA
Gate Body Leakage	V_{GS} = ±20V, V_{DS} = 0V	I_{GSS}	--	--	± 100	nA
Forward Transconductance	V_{DS} ≧50V, I_D = 0.3A	g_{fs}	--	5	--	S
Diode Forward Voltage	I_S = 1A, V_{GS} = 0V	V_{SD}	--	--	1.5	V
Dynamic [b]						
Total Gate Charge	V_{DS} = 400V, I_D = 1A, V_{GS} = 10V	Q_g	--	4.5	6	nC
Gate-Source Charge		Q_{gs}	--	1.1	--	
Gate-Drain Charge		Q_{gd}	--	2	--	
Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	C_{iss}	--	155	200	pF
Output Capacitance		C_{oss}	--	20	26	
Reverse Transfer Capacitance		C_{rss}	--	3	4	
Switching [c]						
Turn-On Delay Time	V_{GS} = 10V, I_D = 1A, V_{DS} = 300V, R_G = 6Ω	$t_{d(on)}$	--	10	30	nS
Turn-On Rise Time		t_r	--	20	50	
Turn-Off Delay Time		$t_{d(off)}$	--	25	45	
Turn-Off Fall Time		t_f	--	24	60	

Notes:
a. Pulse test: pulse width <=300uS, duty cycle <=2%
b. For design reference only, not subject to production testing.
c. Switching time is essentially independent of operating temperature.



Switching Test Circuit



Switchin Waveforms

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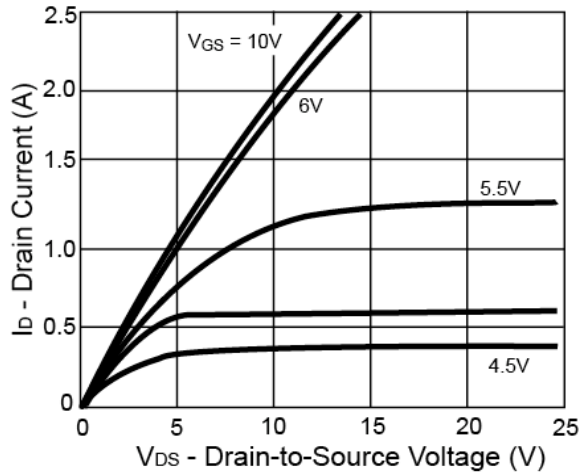
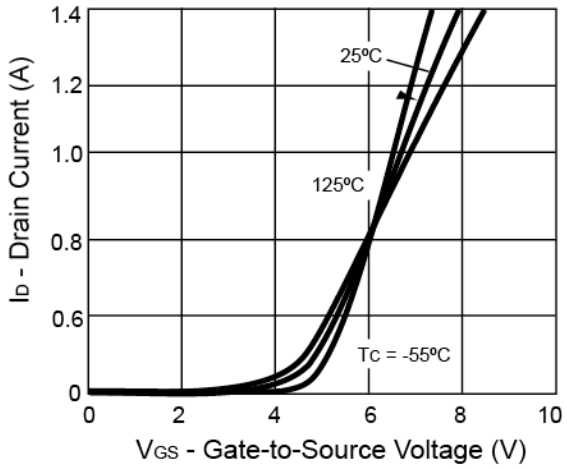
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

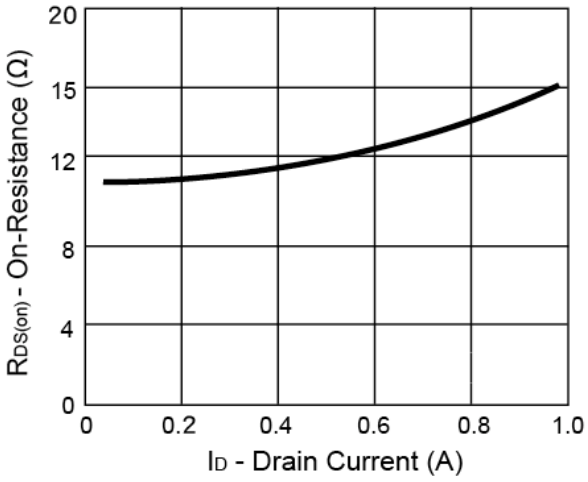
Output Characteristics



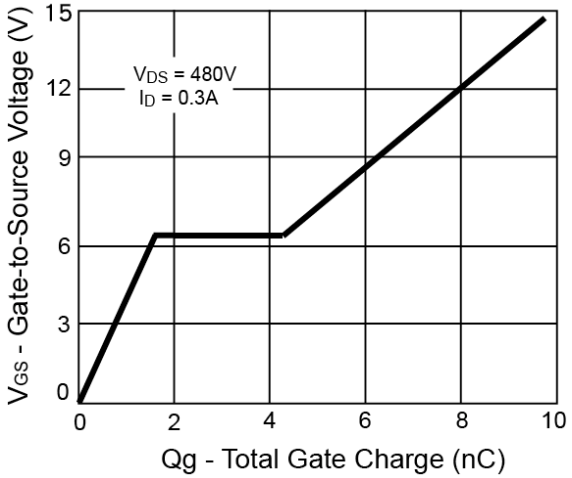
Transfer Characteristics



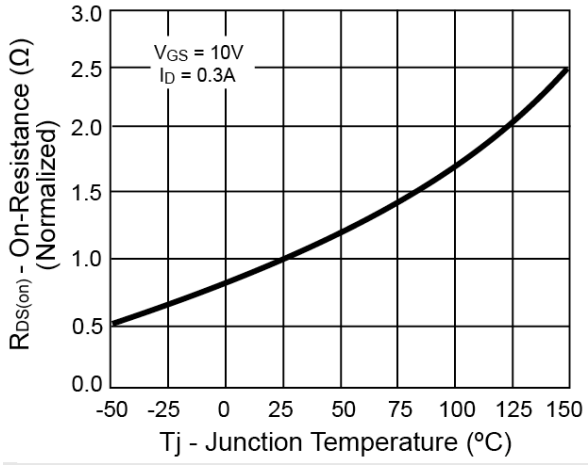
On-Resistance vs. Drain Current



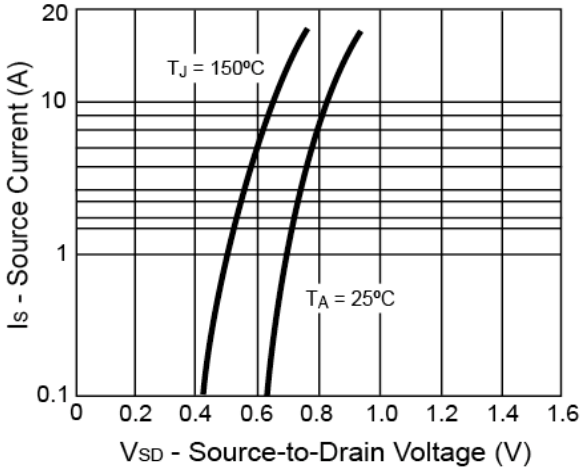
Gate Charge



On-Resistance vs. Junction Temperature

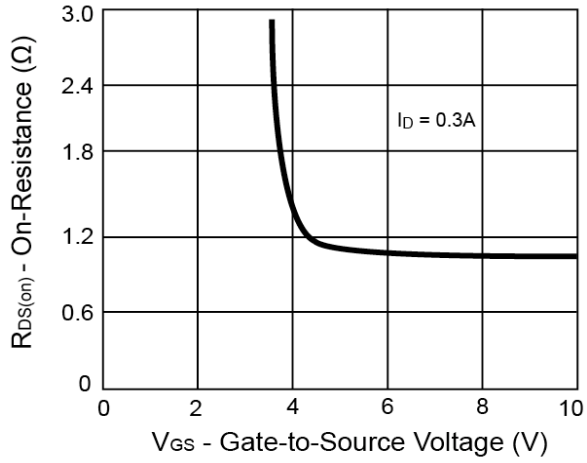


Source-Drain Diode Forward Voltage

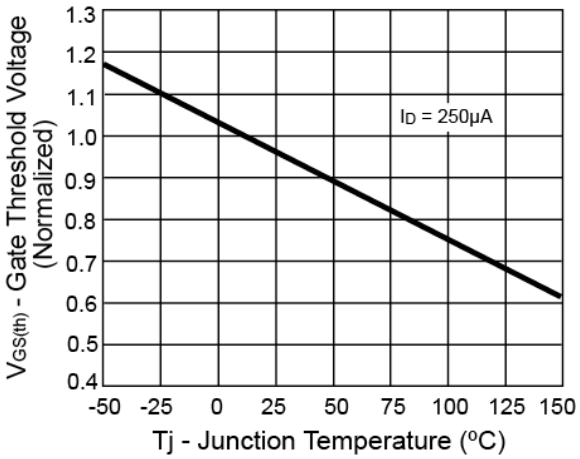


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

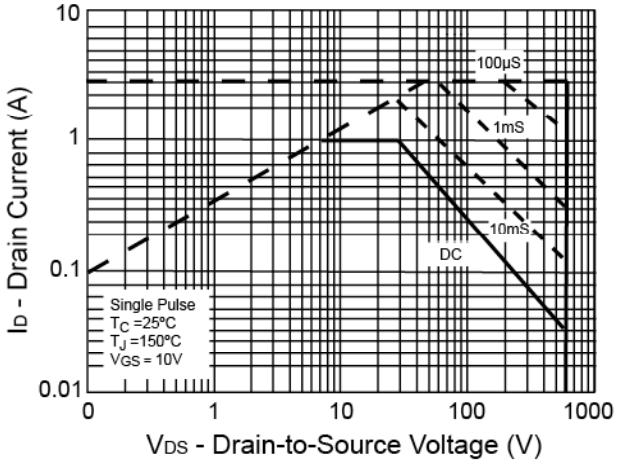
On-Resistance vs. Gate-Source Voltage



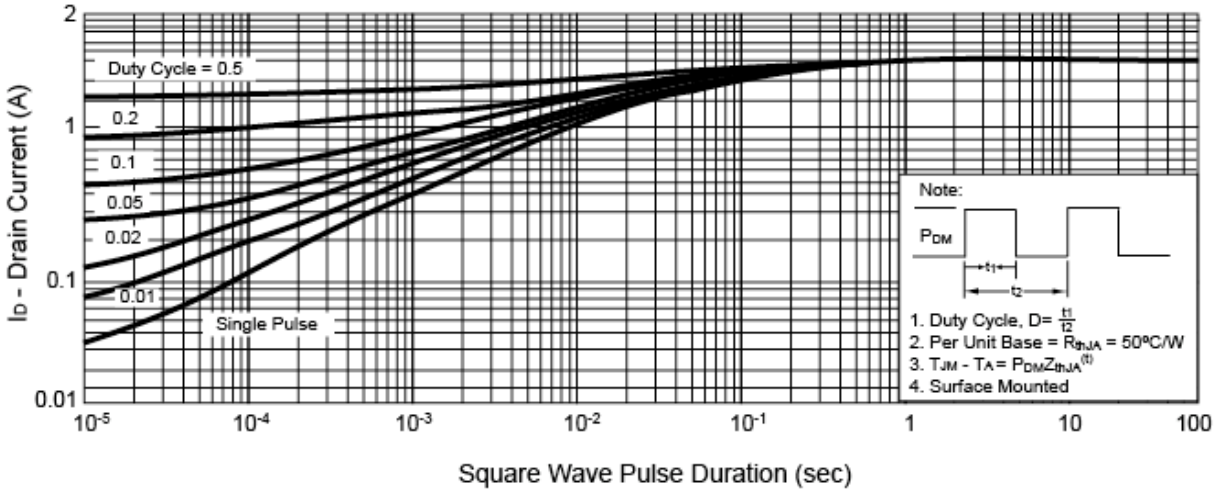
Threshold Voltage



Maximum Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



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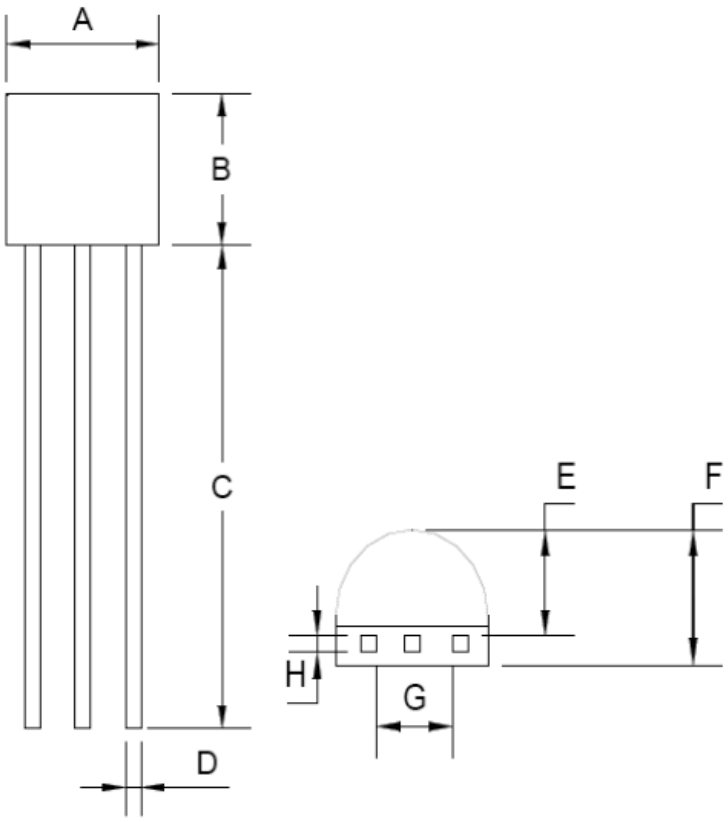
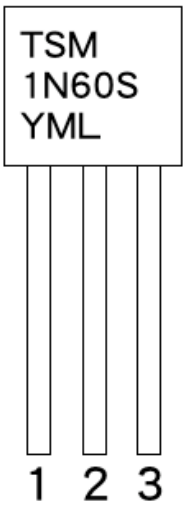
TO-92 Mechanical Drawing



TO-92 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.70	0.169	0.185
B	4.30	4.70	0.169	0.185
C	14.30(typ)		0.563(typ)	
D	0.43	0.49	0.017	0.019
E	2.19	2.81	0.086	0.111
F	3.30	3.70	0.130	0.146
G	2.42	2.66	0.095	0.105
H	0.37	0.43	0.015	0.017

Marking Diagram



Y = Year Code
M = Month Code
(**A**=Jan, **B**=Feb, **C**=Mar, **D**=Apl, **E**=May, **F**=Jun, **G**=Jul, **H**=Aug, **I**=Sep, **J**=Oct, **K**=Nov, **L**=Dec)
L = Lot Code

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